

of displaying the image in accordance with the image data stored in the memory portion provided in said first region.

13. (Amended) A semiconductor device of claim 12, characterized in that power consumed in said semiconductor device by said second display method is 70 % or lower of power consumed in said semiconductor device by said first display method.

14. (Amended) A semiconductor device of claim 12, characterized in that when said second display method is performed, 50 % or higher of power consumed in said semiconductor device is consumed in said first region.

15. (Amended) A semiconductor device of claim 12, characterized in that when said second display method is performed, 90 % or higher of power consumed in said semiconductor device is consumed in said first region.

17. (Amended) A semiconductor device group composed of a first semiconductor device having a function of displaying an image and a second semiconductor device having a function of supplying image data to said first semiconductor device,
said first semiconductor device is a semiconductor device according to any one of claims 1-3, 5-7, or 9, characterized in that,
said semiconductor device group includes a first display method of displaying the image data supplied from said second semiconductor device and a second display method of displaying the image in accordance with the image data stored in the memory portion included in said first semiconductor device.

18. (Amended) A semiconductor device group of claim 17, characterized in that power consumed in the entire said semiconductor device group by said second display method is 70 % or lower of power consumed in said entire semiconductor device group by said first display method.

19. (Amended) A semiconductor device group of claim 17, characterized in that

FOOTNOTES

when said second display method is performed, 50 % or higher of power consumed in said entire semiconductor device group is consumed in said first semiconductor device.

20. (Amended) A semiconductor device group of claim 17, characterized in that when said second display method is performed, 90 % or higher of power consumed in said entire semiconductor device group is consumed in said first semiconductor device.

22. (Amended) A semiconductor device of any one of claims 1-3, 5-7, or 9, characterized in that said memory portion has a memory capacity of 100 kbit to 10 Gbit.

23. (Amended) A semiconductor device according to any one of claims 1-3, 5-7, or 9, characterized in that said memory portion has a memory capacity of 1 Mbit to 128 Mbit.

24. (Amended) A semiconductor device according to any one of claims 1-3, 5-7, or 9, characterized in that said memory portion is composed of one of an SRAM, a DRAM, and an EEPROM.

25. (Amended) A semiconductor device according to any one of claims 1-3, 5-7, or 9, characterized in that said memory portion is composed of a combination of an SRAM, a DRAM, and an EEPROM.

26. (Amended) A semiconductor device according to any one of claims 1-3, 5-7, or 9, characterized in that said semiconductor device is one of an active matrix liquid crystal display device, a passive matrix liquid crystal display device, an active matrix EL display device, and a passive matrix EL display device.

27. (Amended) A semiconductor device according to any one of claims 1-3, 5-7, or 9, characterized in that said semiconductor device is one selected from a display, a video camera, a head mounted display, a DVD player, a goggle type display, a personal computer, a cellular phone, and a car audio system.